

### SOT-23



#### Pin Definition:

1. Gate
2. Source
3. Drain

### PRODUCT SUMMARY

$V_{DS}$ (V)	$R_{DS(on)}$ (m $\Omega$ )	$I_D$ (A)
-20	55 @ $V_{GS} = -4.5V$	-4.0
	85 @ $V_{GS} = -2.5V$	-2.5

### Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

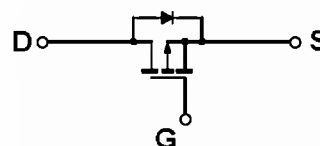
### Application

- Load Switch
- PA Switch

### Ordering Information

Part No.	Package	Packing
TSM2311CX RF	SOT-23	3Kpcs / 7" Reel

### Block Diagram



P-Channel MOSFET

### Absolute Maximum Rating ( $T_a = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	-20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	V
Continuous Drain Current, $V_{GS} @ 4.5V$ .	$I_D$	-4	A
Pulsed Drain Current, $V_{GS} @ 4.5V$	$I_{DM}$	-20	A
Continuous Source Current (Diode Conduction) <sup>a,b</sup>	$I_S$	-0.72	A
Maximum Power Dissipation	$P_D$	$T_a = 25^\circ C$	W
		$T_a = 75^\circ C$	
Operating Junction Temperature	$T_J$	+150	$^\circ C$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	- 55 to +150	$^\circ C$

### Thermal Performance

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	$T_L$	5	S
Junction to Ambient Thermal Resistance (PCB mounted)	$R_{\theta JA}$	250	$^\circ C/W$

#### Notes:

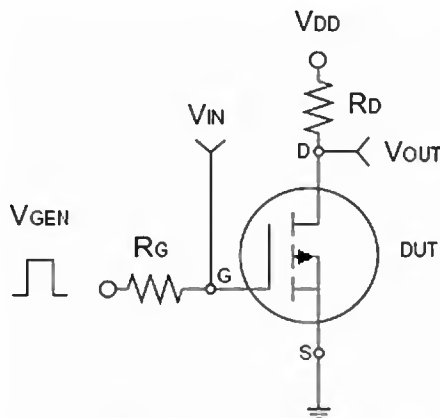
- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board,  $t \leq 5$  sec.
- c. Surface Mounted on FR4 Board,

### Electrical Specifications (Ta = 25°C unless otherwise noted)

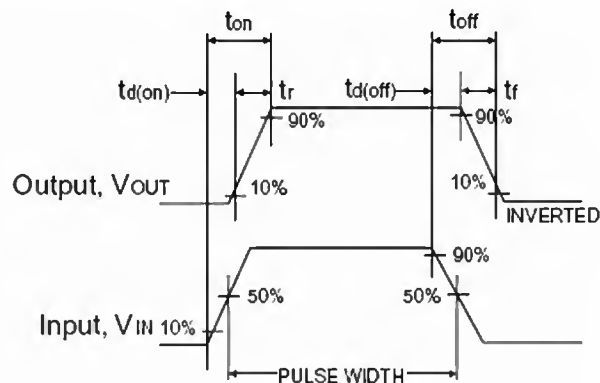
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	$BV_{DSS}$	-20	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	$V_{GS(TH)}$	-0.45	--	-0.95	V
Gate Body Leakage	$V_{GS} = \pm 8V, V_{DS} = 0V$	$I_{GSS}$	--	--	$\pm 100$	nA
Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$	$I_{DSS}$	--	--	-1.0	$\mu A$
On-State Drain Current <sup>a</sup>	$V_{DS} \geq -10V, V_{GS} = -5V$	$I_{D(ON)}$	-6	--	--	A
Drain-Source On-State Resistance <sup>a</sup>	$V_{GS} = -4.5V, I_D = -4A$	$R_{DS(ON)}$	--	45	55	m $\Omega$
	$V_{GS} = -2.5V, I_D = -2.5A$		--	75	85	
Forward Transconductance <sup>a</sup>	$V_{DS} = -5V, I_D = -4A$	$g_{fs}$	--	9	--	S
Diode Forward Voltage	$I_S = -0.75A, V_{GS} = 0V$	$V_{SD}$	--	- 0.8	-1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	$V_{DS} = -6V, I_D = -4A,$ $V_{GS} = -4.5V$	$Q_g$	--	6	9	nC
Gate-Source Charge		$Q_{gs}$	--	1.4	--	
Gate-Drain Charge		$Q_{gd}$	--	1.9	--	
Input Capacitance	$V_{DS} = -6V, V_{GS} = 0V,$ $f = 1.0MHz$	$C_{iss}$	--	640	--	pF
Output Capacitance		$C_{oss}$	--	180	--	
Reverse Transfer Capacitance		$C_{rss}$	--	90	--	
Switching <sup>c</sup>						
Turn-On Delay Time	$V_{DD} = -6V, R_L = 6\Omega,$ $I_D = -1A, V_{GEN} = -4.5V,$ $R_G = 6\Omega$	$t_{d(on)}$	--	22	35	nS
Turn-On Rise Time		$t_r$	--	35	55	
Turn-Off Delay Time		$t_{d(off)}$	--	45	70	
Turn-Off Fall Time		$t_f$	--	25	50	

Notes:

- pulse test:  $PW \leq 300\mu s$ , duty cycle  $\leq 2\%$
- For DESIGN AID ONLY, not subject to production testing.
- Switching time is essentially independent of operating temperature.



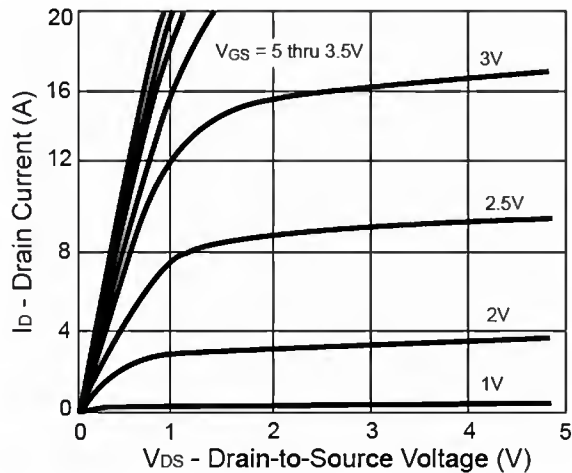
**Switching Test Circuit**



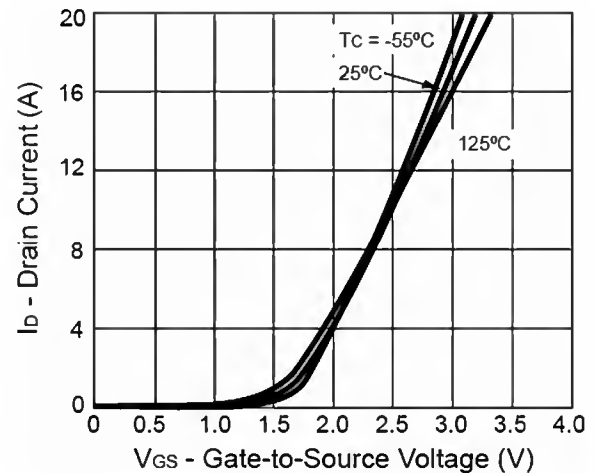
**Switchin Waveforms**

### Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

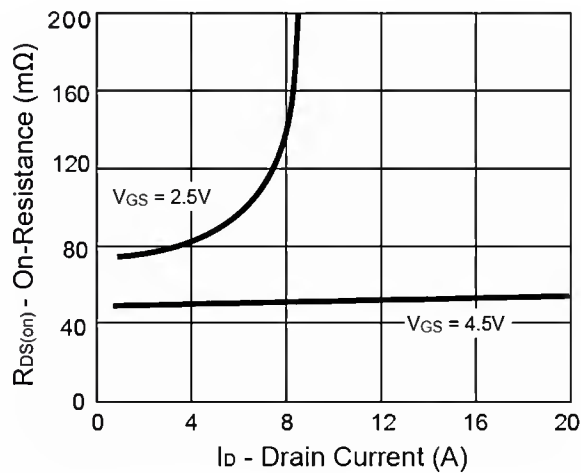
**Output Characteristics**



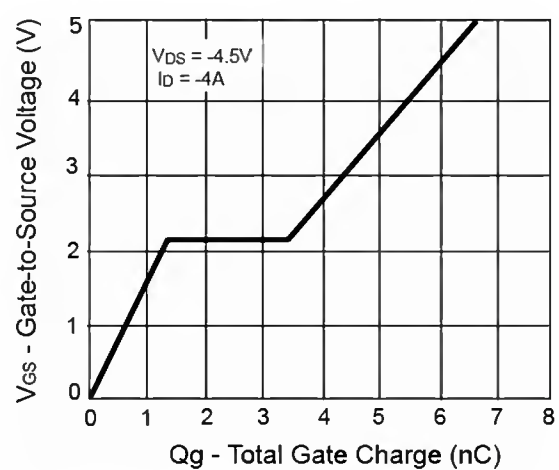
**Transfer Characteristics**



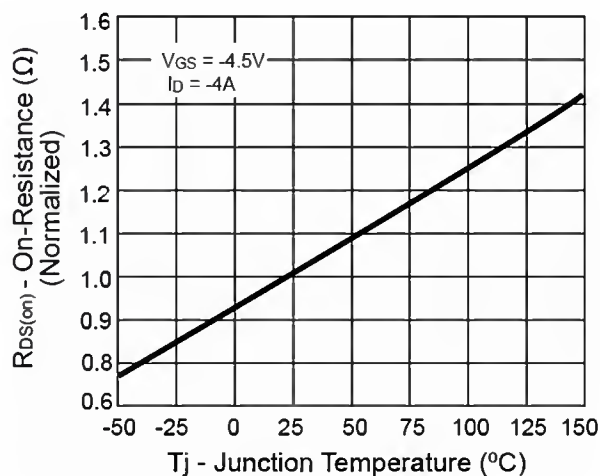
**On-Resistance vs. Drain Current**



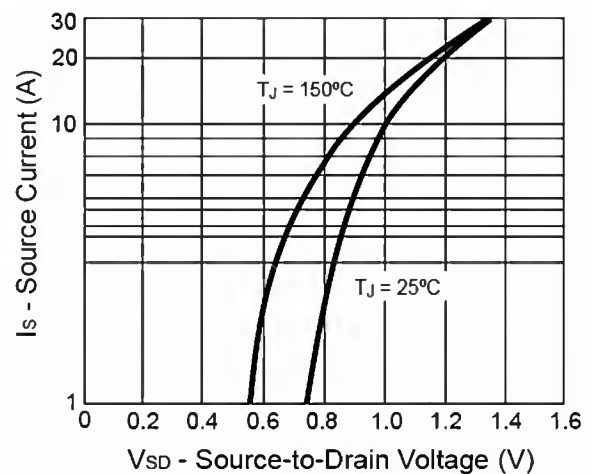
**Gate Charge**



**On-Resistance vs. Junction Temperature**

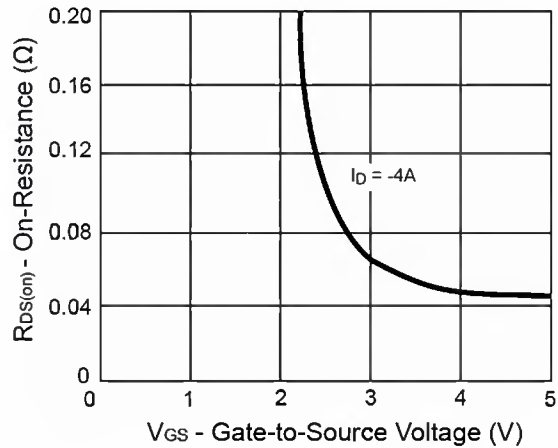


**Source-Drain Diode Forward Voltage**

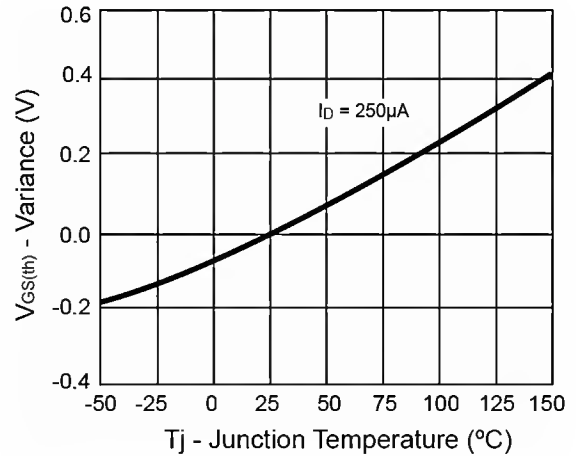


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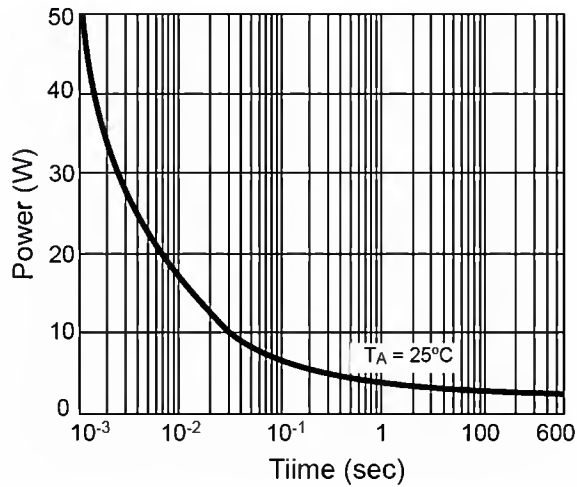
**On-Resistance vs. Gate-Source Voltage**



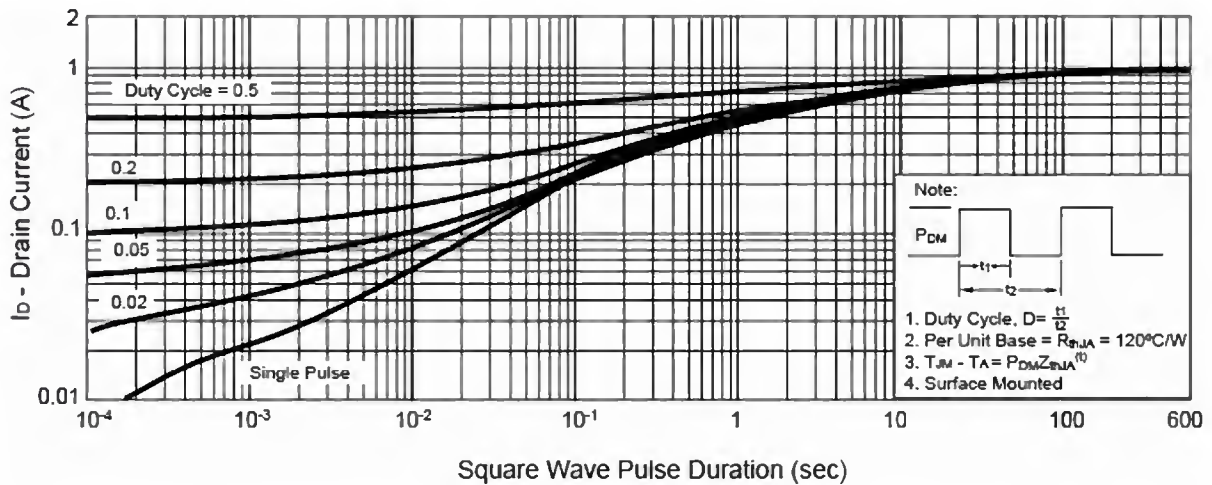
**Threshold Voltage**



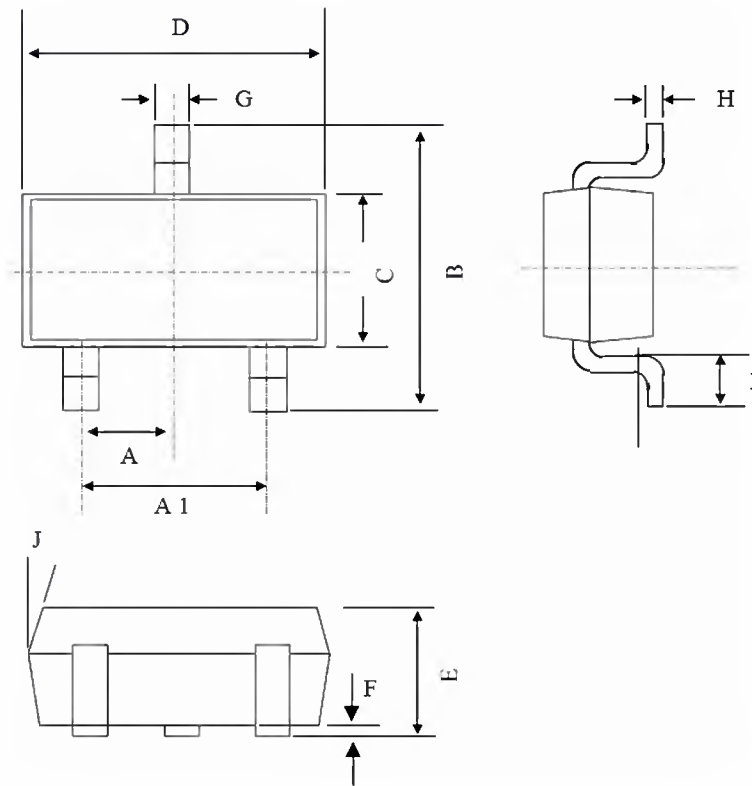
**Single Pulse Power**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

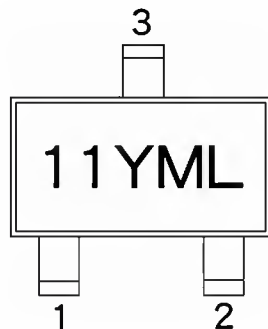


## SOT-23 Mechanical Drawing



SOT-23 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX.
A	0.95 BSC		0.037 BSC	
A1	1.9 BSC		0.074 BSC	
B	2.60	3.00	0.102	0.118
C	1.40	1.70	0.055	0.067
D	2.80	3.10	0.110	0.122
E	1.00	1.30	0.039	0.051
F	0.00	0.10	0.000	0.004
G	0.35	0.50	0.014	0.020
H	0.10	0.20	0.004	0.008
I	0.30	0.60	0.012	0.024
J	5°	10°	5°	10°

## Marking Diagram



**11** = Device Code

**Y** = Year Code

**M** = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug,  
I=Sep, J=Oct, K=Nov, L=Dec)

**L** = Lot Code

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